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SLRS027M - DECEMBER 1976-REVISED FEBRUARY 2013

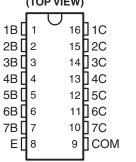
HIGH-VOLTAGE, HIGH-CURRENT DARLINGTON TRANSISTOR ARRAYS

Check for Samples: ULN2002A, ULN2003A, ULN2003AI, ULN2004A, ULQ2003A, ULQ2004A

FEATURES

- 500-mA-Rated Collector Current (Single Output)
- High-Voltage Outputs: 50 V
- Output Clamp Diodes
- Inputs Compatible With Various Types of Logic
- Relay-Driver Applications

ULN2002A ... N PACKAGE
ULN2003A ... D, N, NS, OR PW PACKAGE
ULN2004A ... D, N, OR NS PACKAGE
ULQ2003A, ULQ2004A ... D OR N PACKAGE
(TOP VIEW)



DESCRIPTION

The ULN2002A, ULN2003A, ULN2003AI, ULN2004A, ULQ2003A, and ULQ2004A are high-voltage high-current Darlington transistor arrays. Each consists of seven npn Darlington pairs that feature high-voltage outputs with common-cathode clamp diodes for switching inductive loads. The collector-current rating of a single Darlington pair is 500 mA. The Darlington pairs can be paralleled for higher current capability. Applications include relay drivers, hammer drivers, lamp drivers, display drivers (LED and gas discharge), line drivers, and logic buffers. For 100-V (otherwise interchangeable) versions of the ULN2003A and ULN2004A, see the SN75468 and SN75469, respectively.

The ULN2002A is designed specifically for use with 14-V to 25-V PMOS devices. Each input of this device has a Zener diode and resistor in series to control the input current to a safe limit. The ULN2003A and ULQ2003A have a 2.7-k Ω series base resistor for each Darlington pair for operation directly with TTL or 5-V CMOS devices. The ULN2004A and ULQ2004A have a 10.5-k Ω series base resistor to allow operation directly from CMOS devices that use supply voltages of 6 V to 15 V. The required input current of the ULN/ULQ2004A is below that of the ULN/ULQ2003A, and the required voltage is less than that required by the ULN2002A.



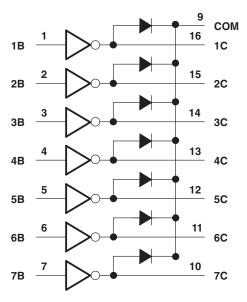


ORDERING INFORMATION⁽¹⁾

T _A	P	ACKAGE ⁽²⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING
			ULN2002AN	ULN2002AN
	PDIP – N	Tube of 25	ULN2003AN	ULN2003AN
			ULN2004AN	ULN2004AN
		Tube of 40	ULN2003AD	
		Reel of 2500	ULN2003ADR	ULN2003A
20°C to 70°C	SOIC - D	Reel of 2500	ULN2003ADRG3	
–20°C to 70°C		Tube of 40	ULN2004AD	LII N2004A
		Reel of 2500	ULN2004ADRG3	ULN2004A
	000 110	Dool of 2000	ULN2003ANSR	ULN2003A
	SOP – NS	Reel of 2000	ULN2004ANSR	ULN2004A
	TSSOP – PW	Tube of 90	ULN2003APW	LINIOOOOA
	1550P – PW	Reel of 2000	ULN2003APWR	UN2003A
	DDID 11	Tub a at 05	ULQ2003AN	ULQ2003A
	PDIP – N	Tube of 25	ULQ2004AN	ULQ2004AN
–40°C to 85°C		Tube of 40	ULQ2003AD	ULQ2003A
-40°C 10 85°C	colo D	Reel of 2500	ULQ2003ADR	ULQ2003A
	SOIC – D	Tube of 40	ULQ2004AD	LII 00004A
		Reel of 2500	ULQ2004ADR	ULQ2004A
	SOP - NS	Reel of 2000	ULN2003AINSR	ULN2003AI
	PDIP – N	Tube of 425	ULN2003AIN	ULN2003AIN
-40°C to 105°C	2010 D	Tube of 40	ULN2003AID	LII NI2002 A I
	SOIC – D	Reel of 2500	ULN2003AIDR	ULN2003AI
	TSSOP - PW	Reel of 2500	ULN2003AIPWR	UN2003AI

⁽¹⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

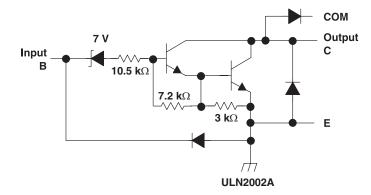
LOGIC DIAGRAM

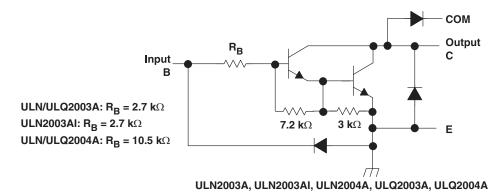


⁽²⁾ Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.



SCHEMATICS (EACH DARLINGTON PAIR)





All resistor values shown are nominal.

The collector-emitter diode is a parasitic structure and should not be used to conduct current. If the collector(s) go below ground an external Schottky diode should be added to clamp negative undershoots.



ABSOLUTE MAXIMUM RATINGS(1)

at 25°C free-air temperature (unless otherwise noted)

			MIN	MAX	UNIT	
V _{CC}	Collector-emitter voltage			50	V	
	Clamp diode reverse voltage ⁽²⁾			50	V	
VI	Input voltage ⁽²⁾			30	V	
	Peak collector current	See Figure 14 and Figure 15		500	mA	
I _{OK}	Output clamp current			500	mA	
	Total emitter-terminal current			-2.5	Α	
		ULN200xA	-20	70		
_	Occupation for a sin to see a section of the sectio	ULN200xAI	-40	105	°C	
T_A	Operating free-air temperature range	ULQ200xA	-40	85	30	
		ULQ200xAT	-40	105		
		D package		73		
^	Declines the send in a decree (3) (4)	N package		67		
θ_{JA}	Package thermal impedance (3) (4)	NS package		64	0000	
		PW package		108	°C/W	
^	Decline at the consoline and consol(5) (6)	D package		36		
θ_{JC}	Package thermal impedance (5) (6)	N package		54		
TJ	Operating virtual junction temperature			150	°C	
	Lead temperature for 1.6 mm (1/16 inch) from case for 10	seconds		260	°C	
T _{stg}	Storage temperature range		-65	150	°C	

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to the emitter/substrate terminal E, unless otherwise noted.
- (3) Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
- (4) The package thermal impedance is calculated in accordance with JESD 51-7.
- (5) Maximum power dissipation is a function of T_J(max), θ_{JC}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is P_D = (T_J(max) T_A)/θ_{JC}. Operating at the absolute maximum T_J of 150°C can affect reliability.
- (6) The package thermal impedance is calculated in accordance with MIL-STD-883.

ELECTRICAL CHARACTERISTICS

 $T_A = 25^{\circ}C$

	DADAMETED	TEST	TEST OF	NDITIONS	UL	UNIT		
	PARAMETER	FIGURE	IESI CC	TEST CONDITIONS		TYP	MAX	UNII
V _{I(on)}	On-state input voltage	Figure 6	V _{CE} = 2 V,	I _C = 300 mA			13	V
			$I_{I} = 250 \mu A$,	$I_C = 100 \text{ mA}$		0.9	1.1	
V _{CE(sat)}	Collector-emitter saturation voltage	Figure 4	$I_{I} = 350 \ \mu A,$	$I_C = 200 \text{ mA}$		1	1.3	V
			$I_{I} = 500 \ \mu A$	$I_C = 350 \text{ mA}$		1.2	1.6	
V_{F}	Clamp forward voltage	Figure 7	I _F = 350 mA			1.7	2	V
		Figure 1	$V_{CE} = 50 \text{ V},$	$I_1 = 0$			50	
I _{CEX}	Collector cutoff current	Figure 2	$V_{CE} = 50 \text{ V},$	$I_1 = 0$			100	μΑ
			gure 2 $T_A = 70^{\circ}C$	$V_I = 6 V$			500	
I _{I(off)}	Off-state input current	Figure 2	$V_{CE} = 50 \text{ V},$	I _C = 500 μA	50	65		μΑ
I	Input current	Figure 3	V _I = 17 V			0.82	1.25	mA
		Figure 6	V 50.V	T _A = 70°C			100	
I _R	Clamp reverse current	Figure 6	V _R = 50 V				50	μA
C _i	Input capacitance		$V_I = 0$,	f = 1 MHz			25	pF





ELECTRICAL CHARACTERISTICS

 $T_A = 25^{\circ}C$

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	DADAMETED	TEST	TEST OF	NIDITIONS	UL	N2003	4	UL	N2004	4	UNIT
	PARAMETER	FIGURE	IESI CC	ONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNII
				I _C = 125 mA						5	
				I _C = 200 mA			2.4			6	
	0	F:	.,	I _C = 250 mA			2.7				.,
$V_{I(on)}$	On-state input voltage	Figure 6	$V_{CE} = 2 V$	I _C = 275 mA						7	V
				I _C = 300 mA			3				
				I _C = 350 mA						8	
			$I_I = 250 \ \mu A$,	I _C = 100 mA		0.9	1.1		0.9	1.1	
$V_{CE(sat)}$	Collector-emitter saturation voltage	Figure 5	$I_1 = 350 \ \mu A$	I _C = 200 mA		1	1.3		1	1.3	V
	Saturation voltage		$I_I = 500 \ \mu A$	I _C = 350 mA		1.2	1.6		1.2	1.6	
		Figure 1	V _{CE} = 50 V,	$I_1 = 0$			50			50	
I_{CEX}	Collector cutoff current	Figure 2	$V_{CE} = 50 \text{ V},$	$I_1 = 0$			100			100	μΑ
		Figure 2	$T_A = 70^{\circ}C$	V _I = 6 V						500	
V _F	Clamp forward voltage	Figure 8	I _F = 350 mA			1.7	2		1.7	2	V
I _{I(off)}	Off-state input current	Figure 3	V _{CE} = 50 V, T _A = 70°C,	I _C = 500 μA	50	65		50	65		μΑ
			V _I = 3.85 V			0.93	1.35				
l _l	Input current	Figure 4	V _I = 5 V						0.35	0.5	mA
			V _I = 12 V						1	1.45	
	01	F:	., 50.1/				50			50	
I_R	Clamp reverse current	Figure 7	$V_R = 50 \text{ V}$	T _A = 70°C			100			100	μA
C _i	Input capacitance		$V_1 = 0$,	f = 1 MHz		15	25		15	25	pF

ELECTRICAL CHARACTERISTICS

 $T_{\Lambda} = 25^{\circ}C$

	DADAMETED	TEST FIGURE	TEST		UL	N2003A	.I	LINUT
	PARAMETER	TEST FIGURE	CONDITIONS		MIN	TYP	MAX	UNIT
				I _C = 200 mA			2.4	
V _{I(on)}	On-state input voltage	Figure 6	V _{CE} = 2 V	I _C = 250 mA			2.7	V
				I _C = 300 mA			3	
			$I_I = 250 \mu A$,	I _C = 100 mA		0.9	1.1	
V _{CE(sat)}	Collector-emitter saturation voltage	Figure 5	$I_I = 350 \mu A$,	I _C = 200 mA		1	1.3	V
			$I_I = 500 \mu A$,	I _C = 350 mA		1.2	1.6	
I _{CEX}	Collector cutoff current	Figure 1	V _{CE} = 50 V,	$I_1 = 0$			50	μΑ
V _F	Clamp forward voltage	Figure 8	I _F = 350 mA			1.7	2	V
I _{I(off)}	Off-state input current	Figure 3	V _{CE} = 50 V,	I _C = 500 μA	50	65		μΑ
I	Input current	Figure 4	V _I = 3.85 V			0.93	1.35	mA
I _R	Clamp reverse current	Figure 7	V _R = 50 V				50	μΑ
Ci	Input capacitance		$V_1 = 0$,	f = 1 MHz		15	25	рF



ELECTRICAL CHARACTERISTICS

 $T_A = -40$ °C to 105°C

	PARAMETER	TEST FIGURE	TEST C	TEST CONDITIONS			.I	UNIT
	PARAMETER	1EST FIGURE	IESI C	TEST CONDITIONS		TYP	MAX	UNIT
				$I_C = 200 \text{ mA}$			2.7	
V _{I(on)}	On-state input voltage	Figure 6	V _{CE} = 2 V	I _C = 250 mA			2.9	V
				I _C = 300 mA			3	
			$I_I = 250 \mu A$,	I _C = 100 mA		0.9	1.2	
V _{CE(sat)}	Collector-emitter saturation voltage	Figure 5	$I_{I} = 350 \ \mu A,$	$I_C = 200 \text{ mA}$		1	1.4	V
			$I_1 = 500 \mu A$,	I _C = 350 mA		1.2	1.7	
I _{CEX}	Collector cutoff current	Figure 1	V _{CE} = 50 V,	I ₁ = 0			100	μΑ
V _F	Clamp forward voltage	Figure 8	I _F = 350 mA			1.7	2.2	V
I _{I(off)}	Off-state input current	Figure 3	V _{CE} = 50 V,	I _C = 500 μA	30	65		μΑ
I	Input current	Figure 4	V _I = 3.85 V			0.93	1.35	mA
I _R	Clamp reverse current	Figure 7	V _R = 50 V				100	μΑ
Ci	Input capacitance		$V_I = 0$,	f = 1 MHz		15	25	pF

ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	DADAMETED	TEST	TEOT OF	TEST CONDITIONS		Q2003	Α	UL	.Q2004 <i>A</i>	A	
	PARAMETER	FIGURE	TEST CC			TYP	MAX	MIN	TYP	MAX	UNIT
				I _C = 125 mA						5	
				I _C = 200 mA			2.7			6	
	On atota langut colling	F:	.,	I _C = 250 mA			2.9				.,
$V_{I(on)}$	On-state input voltage	Figure 6	V _{CE} = 2 V	I _C = 275 mA						7	V
				I _C = 300 mA			3				
				I _C = 350 mA						8	
			$I_1 = 250 \ \mu A$,	$I_C = 100 \text{ mA}$		0.9	1.2		0.9	1.1	
$V_{\text{CE(sat)}}$	Collector-emitter saturation voltage	Figure 5	$I_1 = 350 \ \mu A$,	$I_C = 200 \text{ mA}$		1	1.4		1	1.3	V
	oataration voltage		$I_I = 500 \ \mu A$,	I _C = 350 mA		1.2	1.7		1.2	1.6	
		Figure 1	$V_{CE} = 50 \text{ V},$	$I_1 = 0$			100			50	
I_{CEX}	Collector cutoff current	Figure 2	$V_{CE} = 50 \text{ V},$	$I_1 = 0$						100	μA
		Figure 2	$T_A = 70^{\circ}C$	V _I = 6 V						500	
V_{F}	Clamp forward voltage	Figure 8	$I_F = 350 \text{ mA}$			1.7	2.3		1.7	2	V
$\mathbf{I}_{I(off)}$	Off-state input current	Figure 3	V _{CE} = 50 V, T _A = 70°C,	I _C = 500 μA		65		50	65		μA
			$V_{I} = 3.85 \text{ V}$			0.93	1.35				
II	Input current	Figure 4	$V_I = 5 V$						0.35	0.5	mA
			V _I = 12 V						1	1.45	
	Clamp roverse current	Figure 7	V - 5 0 V	$T_A = 25^{\circ}C$			100			50	
I _R	Clamp reverse current Figure 7 $V_R = 50 \text{ V}$	V _R = 50 V				100			100	μA	
C _i	Input capacitance		$V_{I} = 0,$	f = 1 MHz	-	15	25		15	25	pF

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SWITCHING CHARACTERISTICS

 $T_A = 25^{\circ}C$

PARAMETER		TEST CONDITIONS	ULN2002A ULN	UNIT		
			MIN	TYP	MAX	
t _{PLH}	Propagation delay time, low- to high-level output	See Figure 9		0.25	1	μs
t_{PHL}	Propagation delay time, high- to low-level output	See Figure 9		0.25	1	μs
V_{OH}	High-level output voltage after switching	$V_S = 50 \text{ V}, I_O = 300 \text{ mA}, \text{ See Figure 10}$	V _S - 20			mV

SWITCHING CHARACTERISTICS

 $T_A = 25^{\circ}C$

PARAMETER		TEST CONDITIONS	ULN		UNIT		
	PARAMETER	TEST CONDITIONS	MIN TYP		MAX	ONII	
t _{PLH}	Propagation delay time, low- to high-level output	See Figure 9		0.25	1	μs	
t _{PHL}	Propagation delay time, high- to low-level output	See Figure 9		0.25	1	μs	
V _{OH}	High-level output voltage after switching	$V_S = 50 \text{ V}, I_O \approx 300 \text{ mA}, \text{ See Figure 10}$	V _S - 20			mV	

SWITCHING CHARACTERISTICS

 $T_A = -40$ °C to 105°C

PARAMETER		TEST CONDITIONS	ULN		UNIT		
	PARAMETER	TEST CONDITIONS	MIN TYP MA		MAX	UNII	
t _{PLH}	Propagation delay time, low- to high-level output	See Figure 9		1	10	μs	
t _{PHL}	Propagation delay time, high- to low-level output	See Figure 9		1	10	μs	
V_{OH}	High-level output voltage after switching	$V_S = 50 \text{ V}, I_O \approx 300 \text{ mA}, \text{ See Figure 10}$	V _S -50			mV	

SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST COMPITIONS	ULQ2003/	UNIT		
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH}	Propagation delay time, low- to high-level output	See Figure 9		1	10	μs
t _{PHL}	Propagation delay time, high- to low-level output	See Figure 9		1	10	μs
V_{OH}	High-level output voltage after switching	$V_S = 50 \text{ V}, I_O = 300 \text{ mA}, \text{ See Figure 10}$	V _S - 20			mV



PARAMETER MEASUREMENT INFORMATION

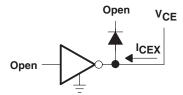


Figure 1. I_{CEX} Test Circuit

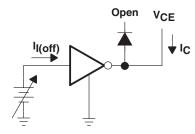


Figure 3. I_{I(off)} Test Circuit

A. I_I is fixed for measuring $V_{CE(sat)}$, variable for measuring h_{FE} .

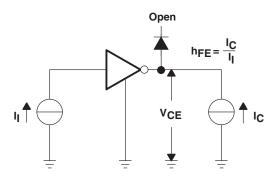


Figure 5. h_{FE}, V_{CE(sat)} Test Circuit

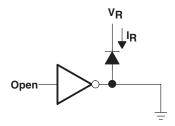


Figure 7. I_R Test Circuit

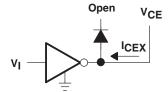


Figure 2. I_{CEX} Test Circuit

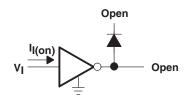


Figure 4. I_I Test Circuit

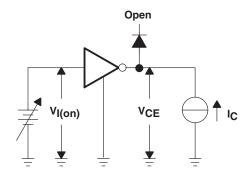


Figure 6. V_{I(on)} Test Circuit

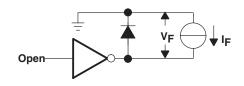


Figure 8. V_F Test Circuit



PARAMETER MEASUREMENT INFORMATION (continued)

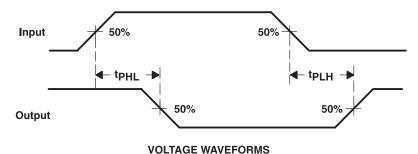
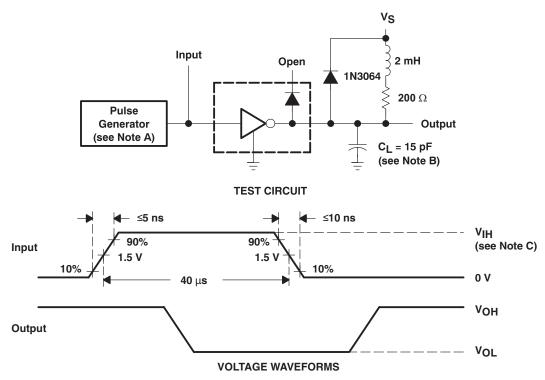


Figure 9. Propagation Delay-Time Waveforms

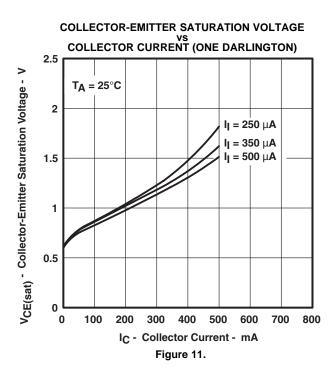


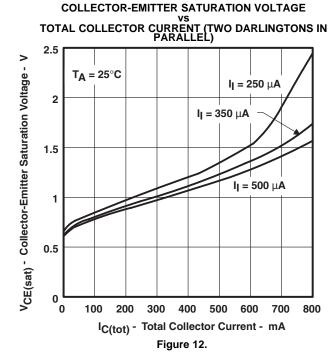
- A. The pulse generator has the following characteristics: PRR = 12.5 kHz, Z_0 = 50 Ω .
- B. C_L includes probe and jig capacitance.
- C. For testing the ULN2003A, ULN2003AI, and ULQ2003A, V_{IH} = 3 V; for the ULN2002A, V_{IH} = 13 V; for the ULN2004A and the ULQ2004A, V_{IH} = 8 V.

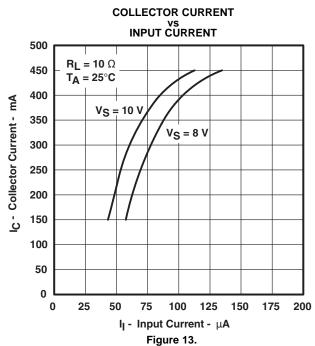
Figure 10. Latch-Up Test Circuit and Voltage Waveforms

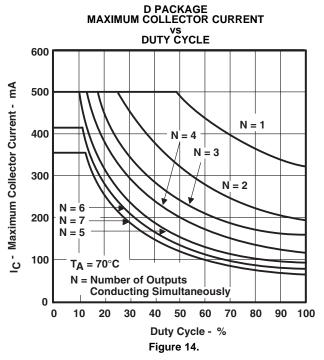


TYPICAL CHARACTERISTICS



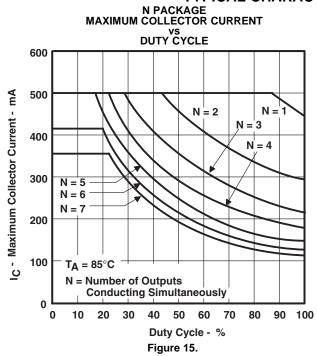


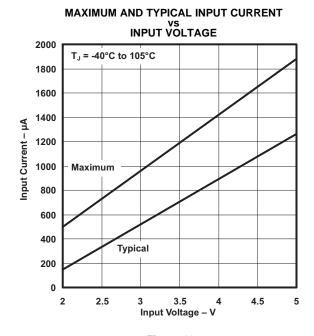


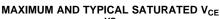




TYPICAL CHARACTERISTICS (continued)







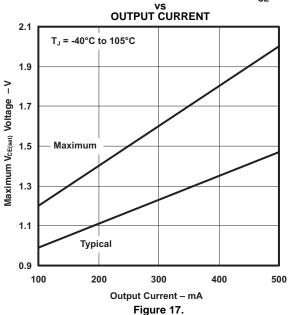
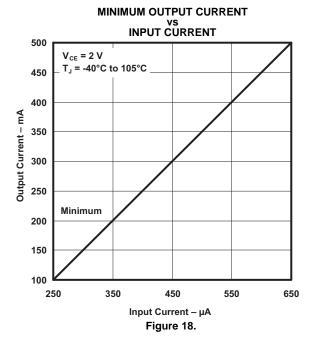


Figure 16.





APPLICATION INFORMATION

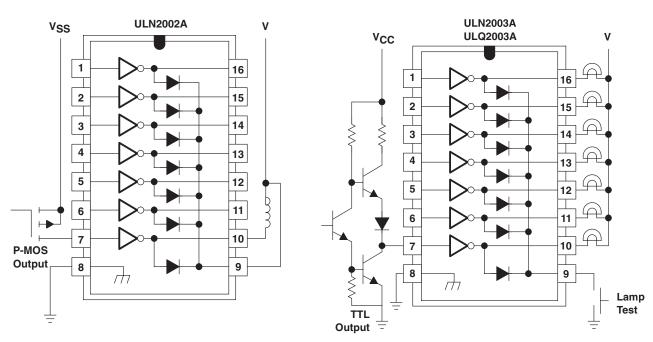


Figure 19. P-MOS to Load

Figure 20. TTL to Load

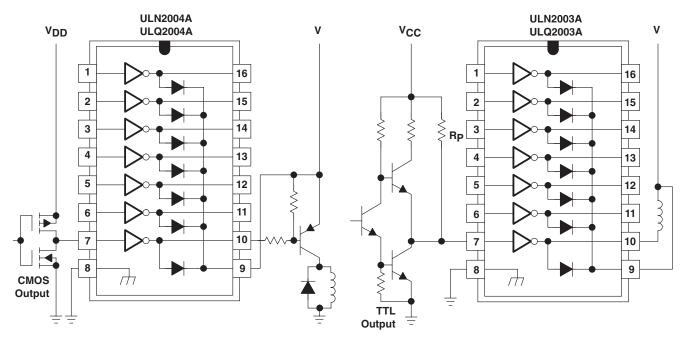
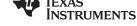


Figure 21. Buffer for Higher Current Loads

Figure 22. Use of Pullup Resistors to Increase Drive Current





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REVISION HISTORY

Changes from Revision K (August 2011) to Revision L	Page
Removed reference to obsolete ULN2001 part	1
Changes from Revision L (March 2012) to Revision M	Page
Updated temperature rating for ULN2003AI in the ORDERING INFORMATION table	2

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18-Jun-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type		Pins		Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Sample
	(1)		Drawing		Qty	(2)		(3)		(4/5)	
ULN2001AD	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI			
ULN2001ADR	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI			
ULN2001AN	OBSOLETE	PDIP	N	16		TBD	Call TI	Call TI			
ULN2002AD	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI			
ULN2002AN	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-20 to 70	ULN2002AN	Sample
ULN2002ANE4	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-20 to 70	ULN2002AN	Sample
ULN2003AD	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	ULN2003A	Sample
ULN2003ADE4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	ULN2003A	Sample
ULN2003ADG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	ULN2003A	Sample
ULN2003ADR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	ULN2003A	Sample
ULN2003ADRE4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	ULN2003A	Sample
ULN2003ADRG3	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-20 to 70	ULN2003A	Sample
ULN2003ADRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	ULN2003A	Sample
ULN2003AID	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 105	ULN2003AI	Sample
ULN2003AIDE4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 105	ULN2003AI	Sample
ULN2003AIDG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 105	ULN2003AI	Sample
ULN2003AIDR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 105	ULN2003AI	Sampl
ULN2003AIDRE4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 105	ULN2003AI	Sampl
ULN2003AIDRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 105	ULN2003AI	Sampl



18-Jun-2013

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
ULN2003AIN	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 105	ULN2003AIN	Sample
ULN2003AINE4	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 105	ULN2003AIN	Sample
ULN2003AINSR	ACTIVE	SO	NS	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to +105	ULN2003AI	Sample
ULN2003AIPW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 105	UN2003AI	Sample
ULN2003AIPWE4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 105	UN2003AI	Sample
ULN2003AIPWG4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 105	UN2003AI	Sample
ULN2003AIPWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 105	UN2003AI	Sample
ULN2003AIPWRE4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 105	UN2003AI	Sample
ULN2003AIPWRG4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 105	UN2003AI	Sample
ULN2003AJ	OBSOLETI	E CDIP	J	16		TBD	Call TI	Call TI	-55 to 125		
ULN2003AN	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-20 to 70	ULN2003AN	Sample
ULN2003ANE3	PREVIEW	PDIP	N	16	25	TBD	Call TI	Call TI	-20 to 70		
ULN2003ANE4	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-20 to 70	ULN2003AN	Sample
ULN2003ANSR	ACTIVE	so	NS	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	ULN2003A	Sample
ULN2003ANSRE4	ACTIVE	so	NS	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	ULN2003A	Sample
ULN2003ANSRG4	ACTIVE	so	NS	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM -20 to 70		ULN2003A	Samples
ULN2003APW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM -20 to 70		UN2003A	Sample
ULN2003APWE4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	UN2003A	Sample
ULN2003APWG4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	UN2003A	Sample





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18-Jun-2013

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty		Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
ULN2003APWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	(3) Level-1-260C-UNLIM	-20 to 70	(4/5) UN2003A	Samples
ULN2003APWRE4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	UN2003A	Samples
ULN2003APWRG4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	UN2003A	Samples
ULN2004AD	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	ULN2004A	Samples
ULN2004ADE4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	ULN2004A	Samples
ULN2004ADG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	ULN2004A	Samples
ULN2004ADR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	ULN2004A	Samples
ULN2004ADRE4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	ULN2004A	Samples
ULN2004ADRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	ULN2004A	Samples
ULN2004AN	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-20 to 70	ULN2004AN	Samples
ULN2004ANE4	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-20 to 70	ULN2004AN	Samples
ULN2004ANSR	ACTIVE	SO	NS	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	ULN2004A	Samples
ULN2004ANSRG4	ACTIVE	SO	NS	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-20 to 70	ULN2004A	Samples
ULQ2003AD	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	ULQ2003A	Samples
ULQ2003ADG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		ULQ2003A	Samples
ULQ2003ADR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	ULQ2003A	Samples
ULQ2003ADRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		ULQ2003A	Samples
ULQ2003AN	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	ULQ2003A	Samples



PACKAGE OPTION ADDENDUM

18-Jun-2013

Orderable Device	Status	Package Type	_	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)		(3)		(4/5)	
ULQ2004AD	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	ULQ2004A	Samples
ULQ2004ADG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		ULQ2004A	Samples
ULQ2004ADR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	ULQ2004A	Samples
ULQ2004ADRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		ULQ2004A	Samples
ULQ2004AN	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-40 to 85	ULQ2004AN	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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PACKAGE OPTION ADDENDUM

18-Jun-2013

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OTHER QUALIFIED VERSIONS OF ULQ2003A, ULQ2004A:

• Automotive: ULQ2003A-Q1, ULQ2004A-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

www.ti.com 8-Apr-2013

TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO P1 BO W Cavity AO

A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ULN2003ADR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
ULN2003ADRG4	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
ULN2003AIDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
ULN2003AIDRG4	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
ULN2003AIPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
ULN2003AIPWR	TSSOP	PW	16	2000	330.0	12.4	7.0	5.6	1.6	8.0	12.0	Q1
ULN2003AIPWRG4	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
ULN2003APWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
ULN2003APWR	TSSOP	PW	16	2000	330.0	12.4	7.0	5.6	1.6	8.0	12.0	Q1
ULN2003APWRG4	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
ULN2004ADR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
ULN2004ADR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
ULN2004ADRG4	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
ULN2004ADRG4	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
ULQ2003ADR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1

www.ti.com 8-Apr-2013



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ULN2003ADR	SOIC	D	16	2500	333.2	345.9	28.6
ULN2003ADRG4	SOIC	D	16	2500	333.2	345.9	28.6
ULN2003AIDR	SOIC	D	16	2500	333.2	345.9	28.6
ULN2003AIDRG4	SOIC	D	16	2500	333.2	345.9	28.6
ULN2003AIPWR	TSSOP	PW	16	2000	367.0	367.0	35.0
ULN2003AIPWR	TSSOP	PW	16	2000	364.0	364.0	27.0
ULN2003AIPWRG4	TSSOP	PW	16	2000	367.0	367.0	35.0
ULN2003APWR	TSSOP	PW	16	2000	367.0	367.0	35.0
ULN2003APWR	TSSOP	PW	16	2000	364.0	364.0	27.0
ULN2003APWRG4	TSSOP	PW	16	2000	367.0	367.0	35.0
ULN2004ADR	SOIC	D	16	2500	333.2	345.9	28.6
ULN2004ADR	SOIC	D	16	2500	367.0	367.0	38.0
ULN2004ADRG4	SOIC	D	16	2500	367.0	367.0	38.0
ULN2004ADRG4	SOIC	D	16	2500	333.2	345.9	28.6
ULQ2003ADR	SOIC	D	16	2500	333.2	345.9	28.6

14 LEADS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



D (R-PDS0-G16)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G16)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



PW (R-PDSO-G16)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



MECHANICAL DATA

NS (R-PDSO-G**)

14-PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



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